

Letters to the Editor

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Mass-Spectrographic Identification of Cm²⁴³ and Cm²⁴⁴

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THE isotopes Cm²⁴³ and Cm²⁴⁴ have been identified mass-spectrographically. The curium fraction from a long neutron irradiation of Am²⁴¹ was separated chemically and its isotopic composition determined by means of the 60° focusing mass spectrograph used in this laboratory for work with radioactive isotopes. A thermal ion source was used and the ions were recorded photographically. Figure 1 is a reproduction of the plate obtained.

The Am²⁴¹ which is responsible for the rather intense line at mass 241 and the much fainter line at mass 257 (Am²⁴¹O⁺) represents a very small fraction of the initial Am²⁴¹ target material that was not successfully separated in the chemistry. The line at mass 254 is due to Pu²³⁸O⁺ which grew in from the alpha-decay of

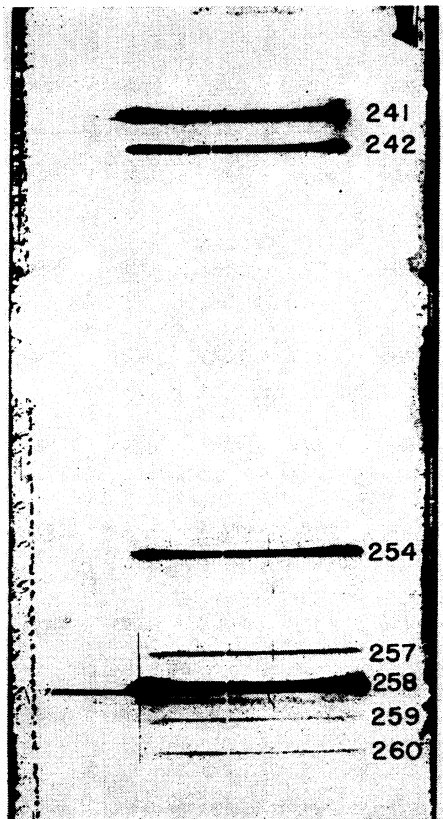
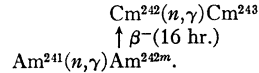


FIG. 1. Isotopic composition of the curium fraction from a long neutron irradiation of Am²⁴¹.

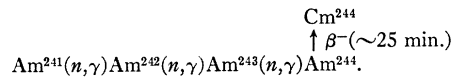
Cm²⁴² after the chemical separation. The Cm²⁴² appears to a small extent as the metal at mass 242 and much more intensely as Cm²⁴²O⁺ at mass 258. The ghost line one-third of a mass unit to the right of mass 258 is a characteristic of the machine and appears often on intense spectra. The isotopes Cm²⁴³ and Cm²⁴⁴ because of their small abundances are detected only at the more intense oxide masses 259 and 260.

A photometer tracing of the plate gave the semiquantitative information that Cm²⁴³ and Cm²⁴⁴ are of about equal abundance in this sample and that each is about 1 percent as abundant as Cm²⁴².

The Cm²⁴³ was produced by the following sequence of nuclear reactions:



The Cm²⁴⁴ was undoubtedly produced both by neutron capture in the Cm²⁴³ formed as above and also by the following path:¹



Alpha-particles ascribed to Cm²⁴³ have been seen previously,^{2,3} but the mass spectrographic identification of Cm²⁴⁴ represents the first definite evidence for this isotope.

From the energy balances involved one expects Cm²⁴³ to be slightly unstable with respect to orbital electron capture,¹ or possibly beta-stable. The alpha-decay systematics⁴ predict that Cm²⁴⁴ is beta-stable with an alpha-decay half-life of years.

We would like to express our appreciation to Dr. S. G. Thompson for his very valuable assistance in carrying out this work.

* This work was performed under the auspices of the AEC.
¹ Street, Giorso, and Seaborg, Phys. Rev. **79**, 530 (1950).
² Street, Thompson, and Giorso (unpublished work).
³ Rasmussen, Reynolds, Thompson, and Giorso, Phys. Rev. **80**, 475 (1950).
⁴ Perlman, Giorso, and Seaborg, Phys. Rev. **77**, 26 (1950).

P-N Junctions Prepared by Impurity Diffusion

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WHEN P-N barriers in a semiconductor are formed by the solidification of a melt, the concentrations of the different impurities which are present vary nearly linearly with distance from the barrier. The rectification properties of such barriers depend upon the donor and acceptor impurity gradients in such a manner that as the net concentration gradient is increased, the forward characteristic improves while the inverse breakdown voltage decreases.

By using a distinctly non-linear impurity distribution as indicated by Fig. 1, it is possible to construct rectifiers which combine the good forward characteristic of a large impurity gradient with the high inverse breakdown voltage of a barrier having a small impurity gradient. In the blocking direction, the potential drop is largely confined to a thin "barrier layer" within which the impurity concentration varies slowly. In the forward direction, holes and electrons are drawn in opposite directions across the rectifier from the regions of high impurity concentration where a copious supply of carriers is available. If the layers of high impurity concentration are not too greatly separated, space charge potentials due to recombination of holes and electrons can be made small and good forward characteristics are obtained.

The non-linear impurity distribution which is required may be obtained by thermal diffusion of donor and acceptor impurities into opposite sides of a wafer of semiconductor. Germanium diodes have been prepared in this manner which will withstand inverse potentials of the order of 100 volts and which will pass 500 amp./cm² at one volt in the forward direction. The charac-

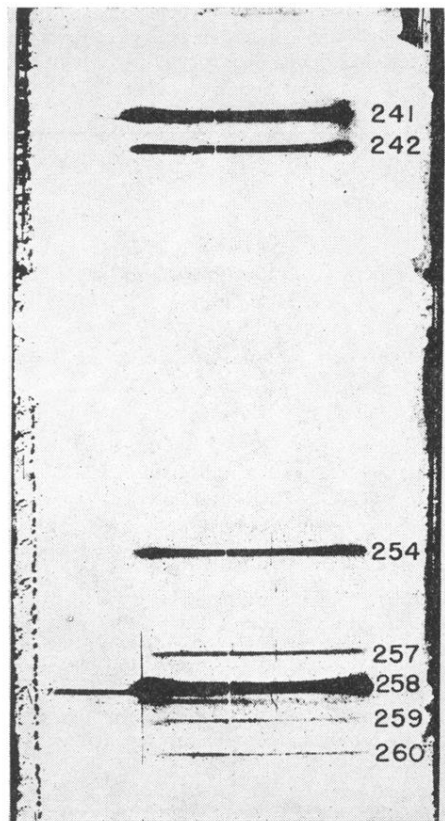


FIG. 1. Isotopic composition of the curium fraction from a long neutron irradiation of Am^{241} .